

Lecture 3: Benefits of Scaling II

- Announcements:
- As announced last time, I am on travel right now
- This is a pre-recorded video
- The notes from last time are online, as well as the video - both in the Lecture link table
- Modules 1 & 2 are online (also, in the Lecture link table)
- Get your computer accounts by following the instructions at the end of the Course Info Sheet
- HW#1 is online and due Thursday, Feb. 1, at 10 a.m. in the EE247B/ME218 Homework Box near 140 Cory
- Kieran posted some info on where to go for office hours in the coming weeks (it's different from the course info sheet, which was tentative)
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- Today:
- Reading: Senturia, Chapter 1
- Lecture Topics:
 - ↳ Benefits of Miniaturization
 - ↳ Examples
 - GHz micromechanical resonators
 - Chip-scale atomic clock
 - Micro gas chromatograph
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- Last Time:
- Going through Module 2, looking at how scaling vibrating RF MEMS provides both benefits and problems that one must circumvent
- Continue with this now

Scaling: 2x, 1/2x
↓

① Scale all dimension equally by a factor S

$$f_0 \sim \frac{S}{S^2} = \frac{1}{S}$$

② If scale L only: $f_0 = \frac{1}{S^2}$ → even faster rise in freq!
(...but problems...)

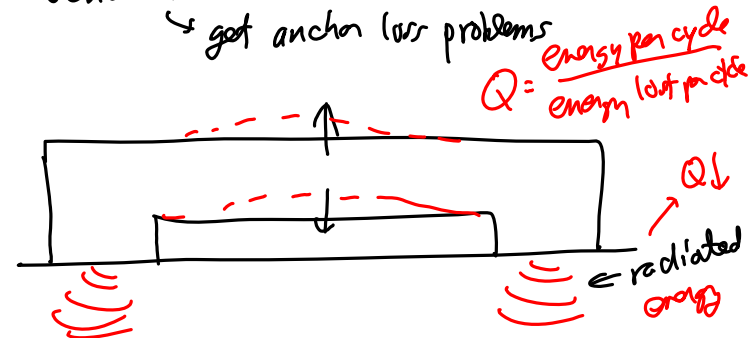
Example.

$$L = 4 \mu\text{m} \rightarrow f_0 = (1.03)(8076) \frac{2\mu}{(4\mu)^2} = 1.04 \text{ GHz}$$

ignore width effect → really need $\sim 3 \mu\text{m}$
questionable thing to do

Remarks.

- ① Eq.(1) not accurate when $L \approx W \approx h$
- ② When $L \approx h$ (a when it isn't more than $10 \times h$)
↳ get anchor loss problems



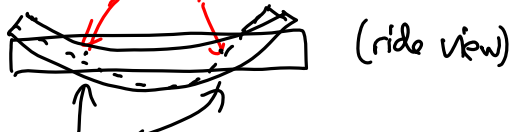
↓
Soln:

③ Solution: use nanodimensional! ✓
 ex. $h=200\text{nm}$, $L \sim 1\mu\text{m}$
 $k = \text{small}$
 \rightarrow very little anchor loss $\rightarrow Q \sim 1,000$

↓
Problem: power handling ↓ when size ↓
 ↓
Soln: use massive numbers in arrays

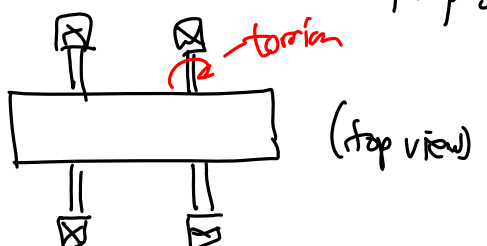
④ Better Soln: use other geometries

Free-Free Beam: nodal points



(side view)

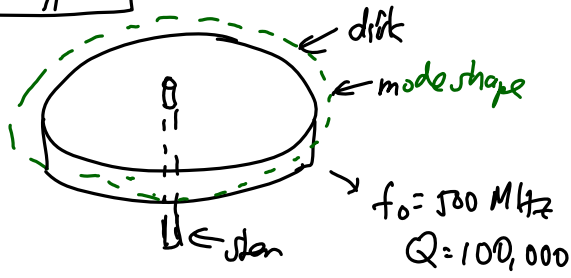
no vertical motion → less loss from pumping into the substrate



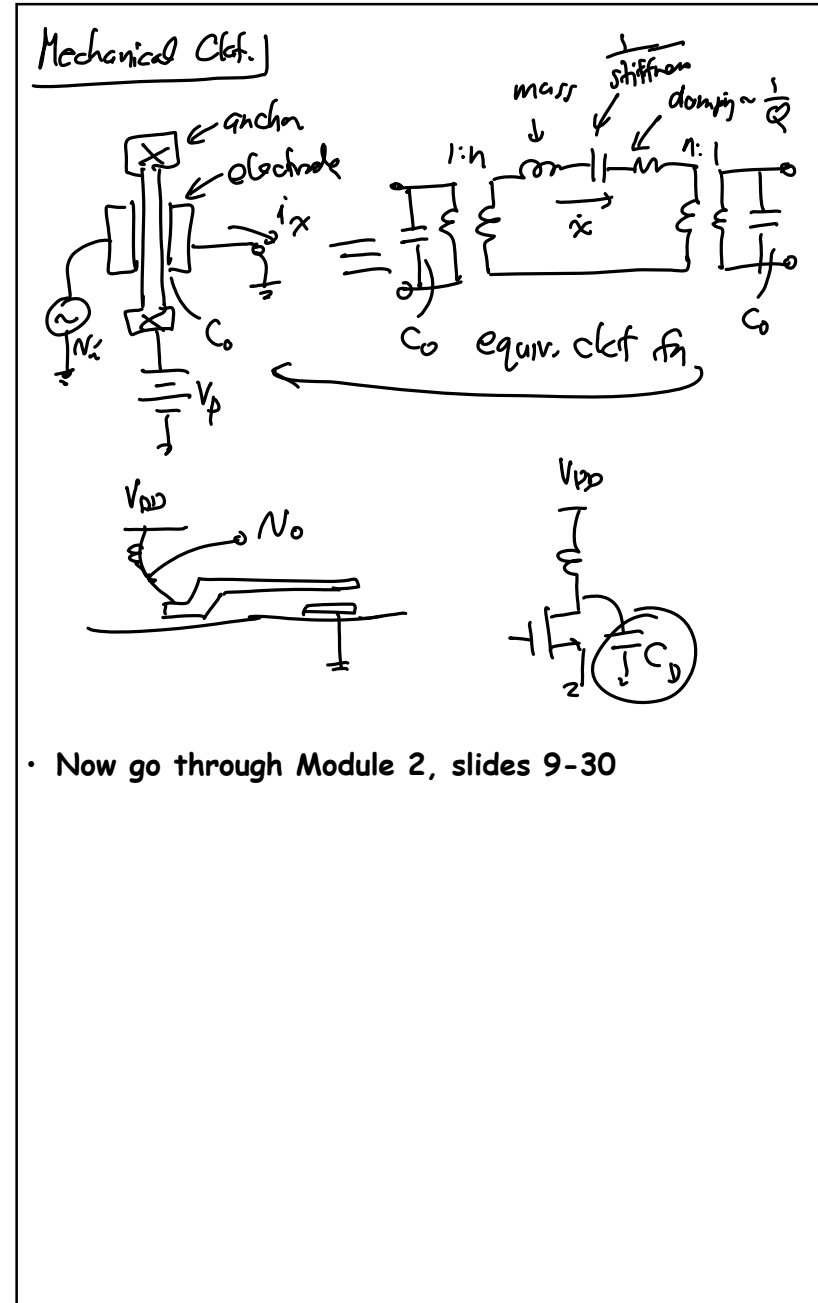
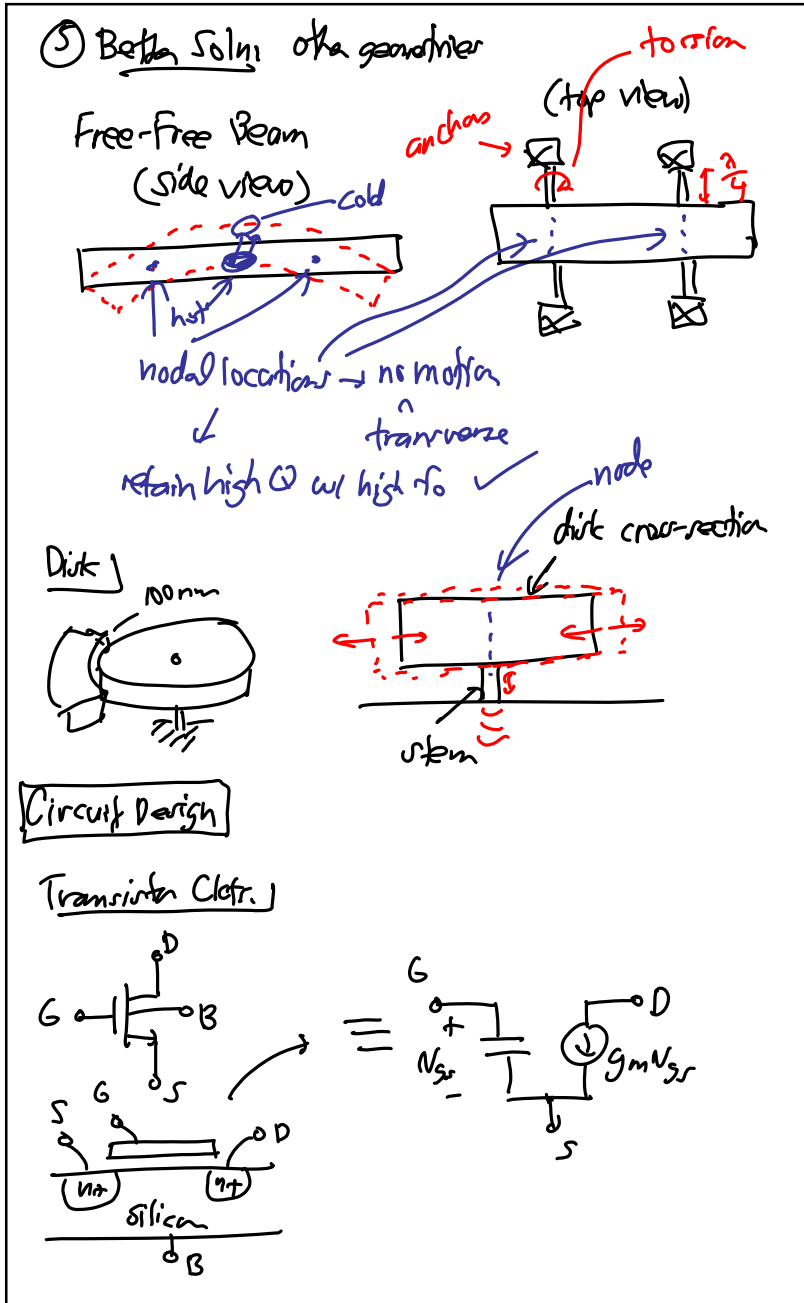
(top view)

torsion

Even Better Approach



disk
 mode shape
 $f_0 = 500\text{ MHz}$
 $Q = 100,000$
 Stan



Review Electrical Resistance First
(then attack the thermal R analogy)

l : length
 w : width
 h : height
 cross-sectional area = $A = hw$

$R_e \triangleq$ electrical resistance = $\frac{l}{\sigma A}$
 \uparrow electrical conductivity

C_e : capacitance = $\frac{\epsilon_0 \epsilon_r WL}{d}$
 \uparrow permittivity

\hookrightarrow Stored Energy (charge energy) = $\frac{1}{2} CV^2 = E$
 \uparrow voltage across the capacitor

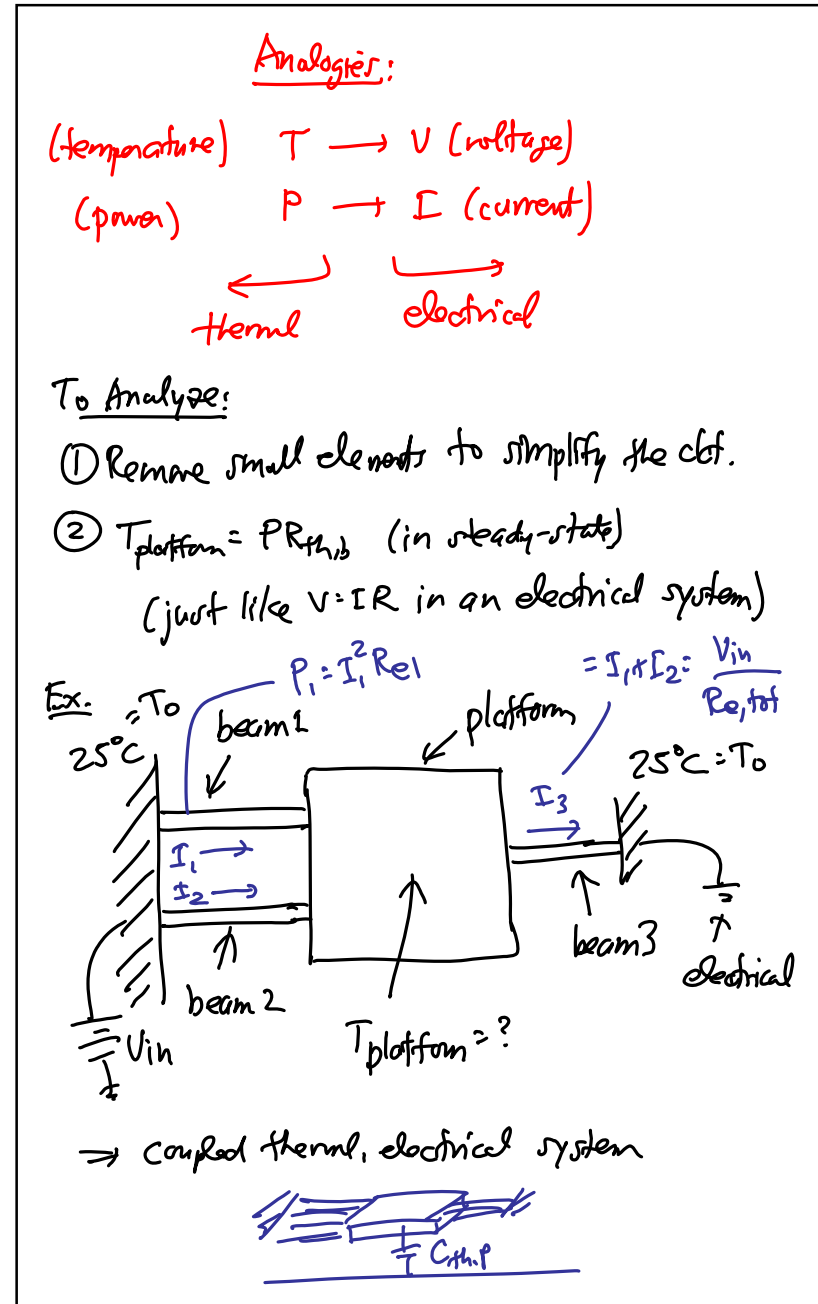
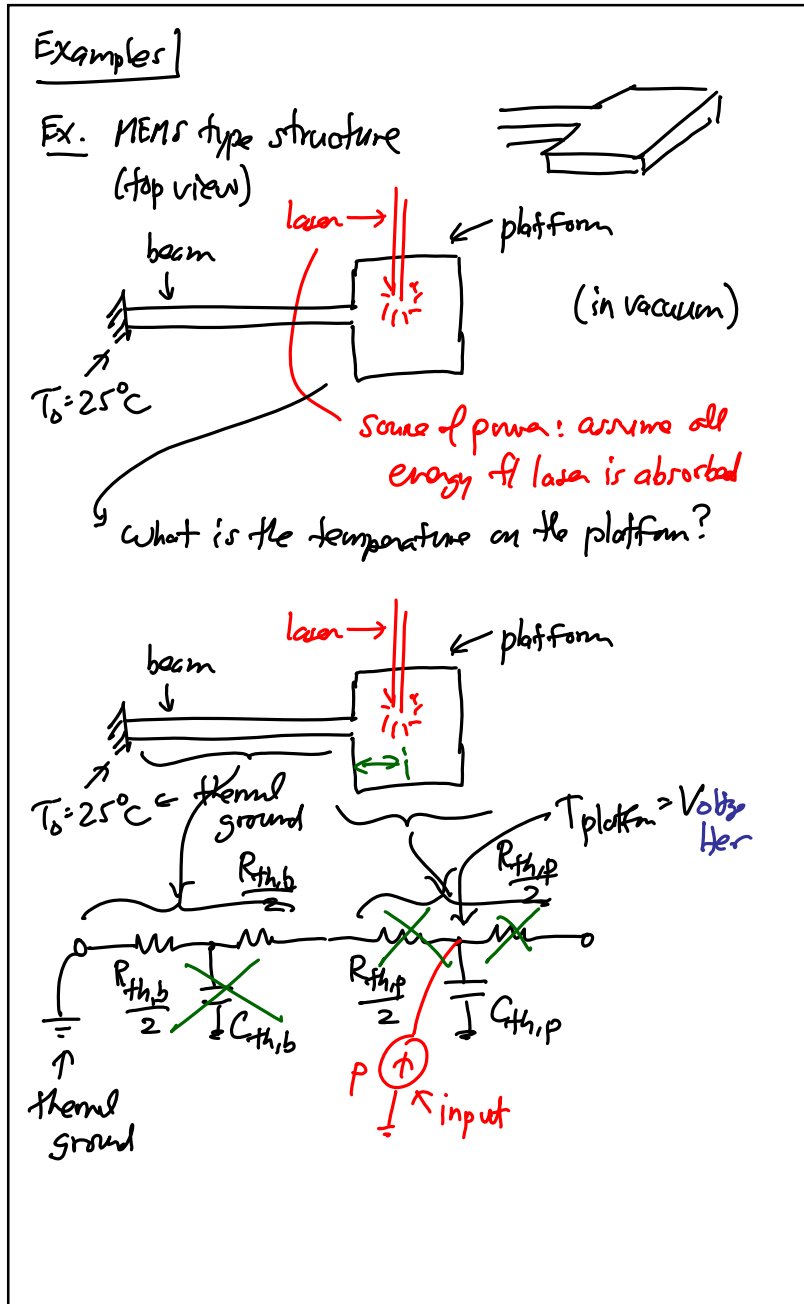
\Rightarrow if want to be more exact:

Thermal Ckt.

$A = hw$

\Rightarrow thermal capacitance: $C_{th} = \rho V C_p$
 \uparrow density
 \downarrow volume
 \leftarrow specific heat
 \rightarrow stores thermal energy

\Rightarrow thermal resistance:
 $R_{th} = \frac{l}{kA}$
 \uparrow thermal conductivity
 \leftarrow cross-sectional area
 \leftarrow length



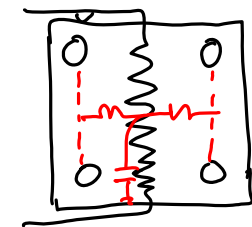
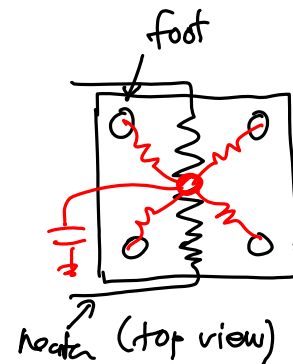
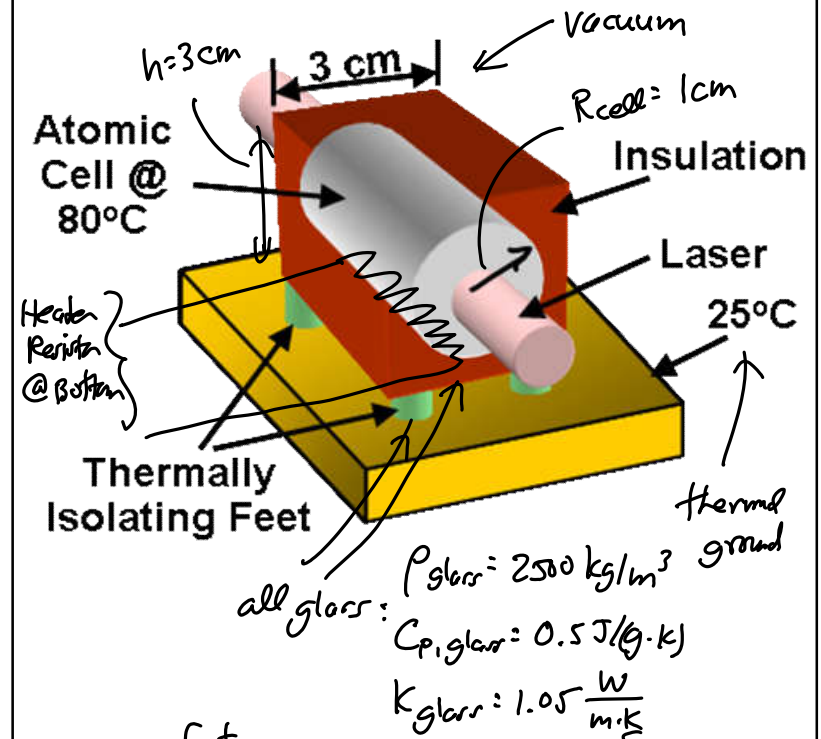
⇒ Draw the thermal ckt.

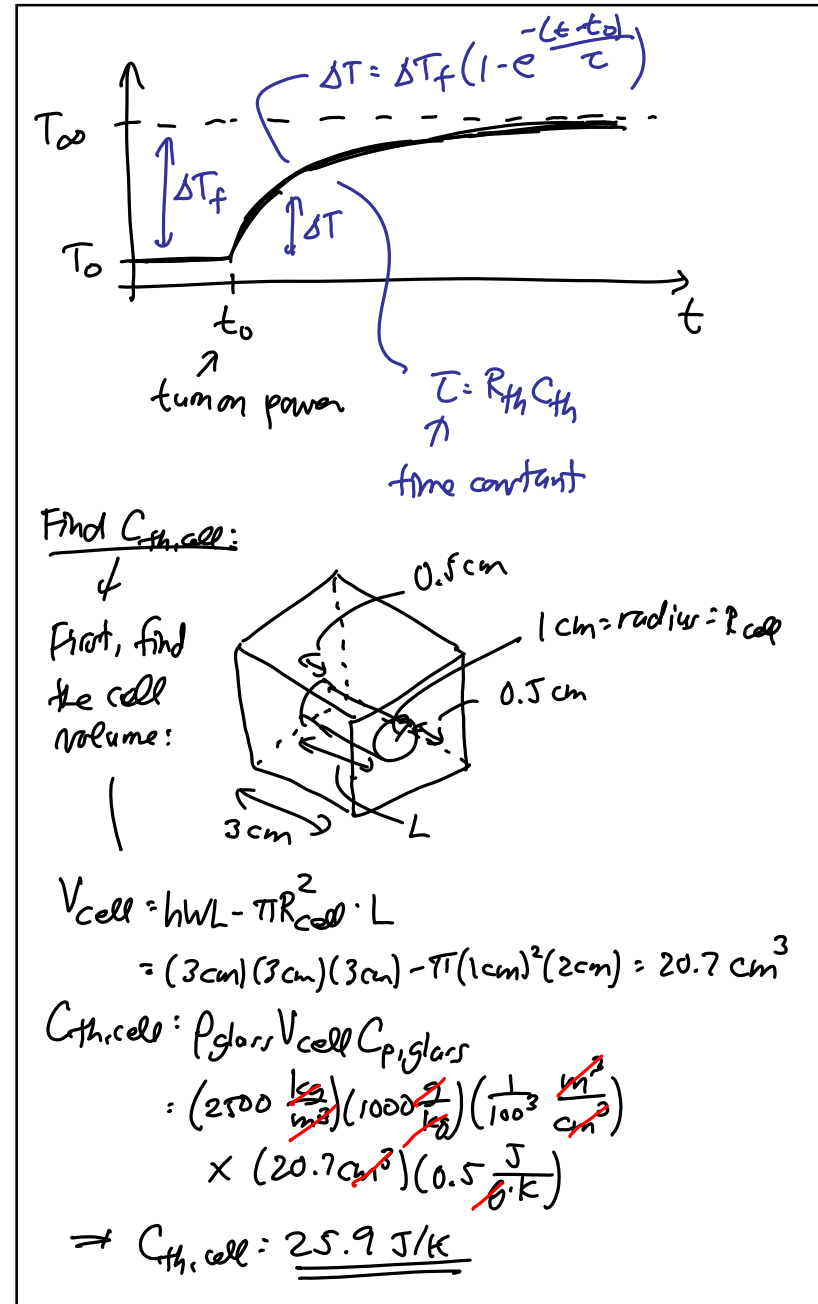
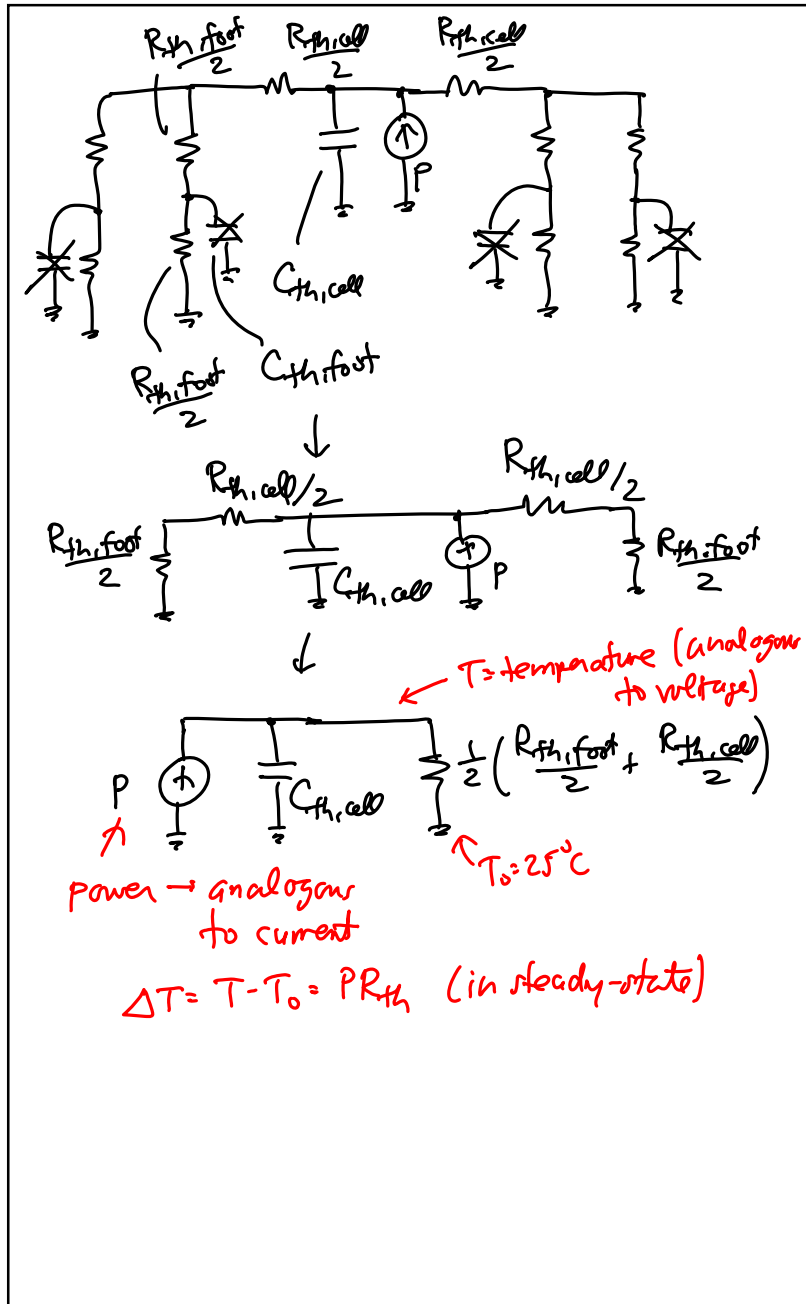
To Analyze:

- ① $I_3 = I_1 + I_2 = \frac{V_{in}}{R_{e, tot}}$ (electrical analysis)
- ② Get P_i 's. (power)
- ③ Use superposition to solve the thermal ckt.
handle one power source at a time & sum the temperatures (i.e., thermal voltages) to get the total temperature at any node

Example: Thermal Ckt.

⇒ determine the power needed to get this atomic cell to 80°C (from RT) & how fast





Find $\frac{R_{th,cell}}{2}$

$\frac{R_{th,cell}}{2} = \frac{\frac{3}{4}}{k(3)(\frac{1}{2})} + \frac{\frac{3}{4}}{k(3)(1)} = \frac{1}{k}(\frac{1}{2} + \frac{1}{4}) = \frac{3}{4} \frac{1}{k}$

$[R_{th} = \frac{l}{kA}] \quad \therefore \frac{R_{th,cell}}{2} = \frac{3}{4} \frac{1}{1.05} \times (100 \frac{cm}{m})$

$= \underline{\underline{35.7 \text{ K/W}}}$